

N-Channel 30-V (D-S) 175 °C MOSFET

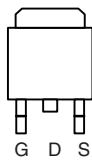
PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0025 at $V_{GS} = 10$ V	110 ^a

FEATURES

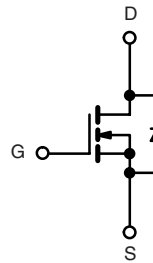
- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- High Threshold Voltage


 Available
RoHS*
 COMPLIANT

TO-263


Top View

DRAIN connected to TAB

Ordering Information: SUM110N03-03
 SUM110N03-03-E3 (Lead (Pb)-free)


N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	110 ^a
		$T_C = 100$ °C	110 ^a
Pulsed Drain Current	I_{DM}	350	A
Avalanche Current	I_{AR}	70	
Repetitive Avalanche Energy ^b	E_{AR}	245	mJ
Maximum Power Dissipation ^b	P_D	$T_C = 25$ °C	242 ^c
		$T_A = 25$ °C ^d	3.75
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case	R_{thJC}	0.62	

Notes:

- Package limited.
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).

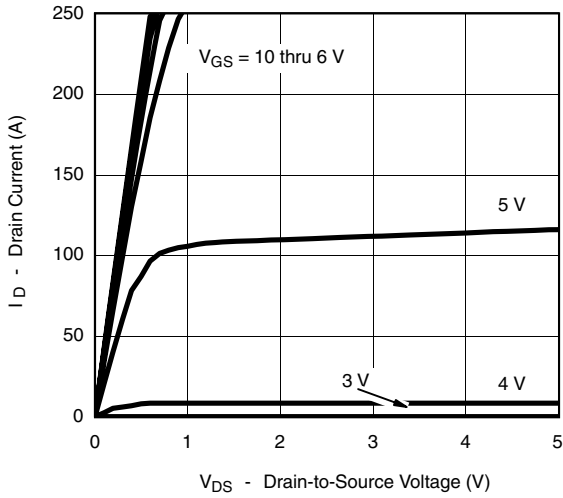
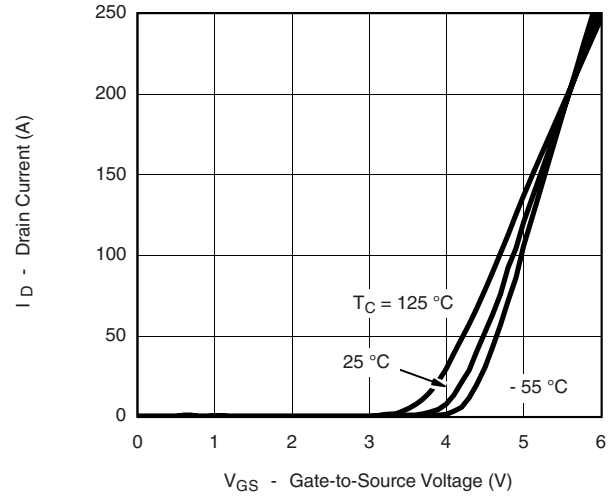
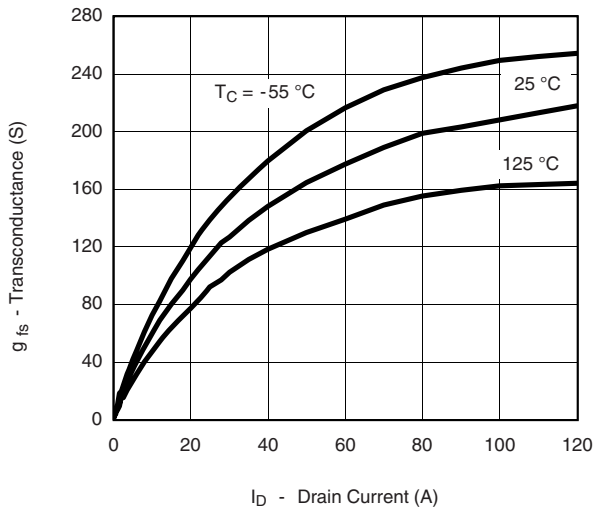
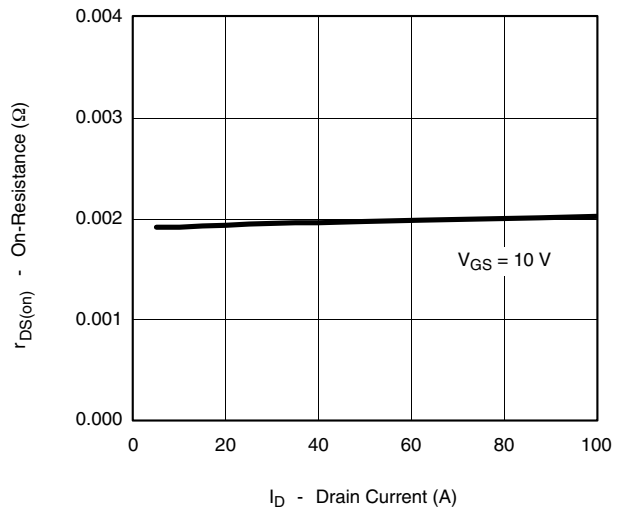
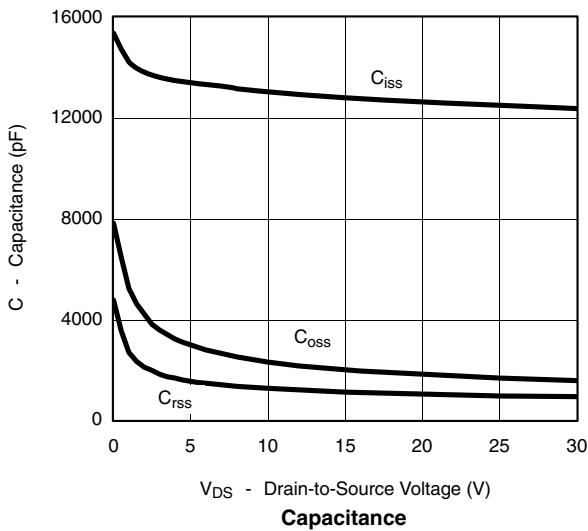
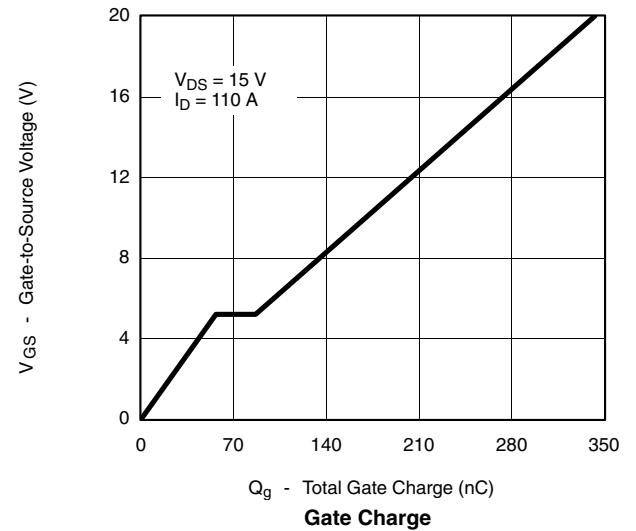
* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.002	0.0025	Ω
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.0037	
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.0044	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	15			S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		12500		pF
Output Capacitance	C_{oss}			1650		
Reverse Transfer Capacitance	C_{rss}			970		
Total Gate Charge ^b	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 110\text{ A}$		170	250	nC
Gate-Source Charge ^b	Q_{gs}			57		
Gate-Drain Charge ^b	Q_{gd}			30		
Turn-On Delay Time ^b	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.18\text{ }\Omega$ $I_D \cong 110\text{ A}, V_{GEN} = 10\text{ V}, R_G = 2.5\text{ }\Omega$		20	35	ns
Rise Time ^b	t_r			125	190	
Turn-Off Delay Time ^b	$t_{d(off)}$			70	105	
Fall Time ^b	t_f			25	40	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}^c$						
Continuous Current	I_S				110	A
Pulsed Current	I_{SM}				350	
Forward Voltage ^a	V_{SD}	$I_F = 50\text{ A}, V_{GS} = 0\text{ V}$		0.9	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		70	140	ns
Peak Reverse Recovery Charge	I_{RM}			3	4.5	A
Reverse Recovery Charge	Q_{rr}			0.1	0.31	μC

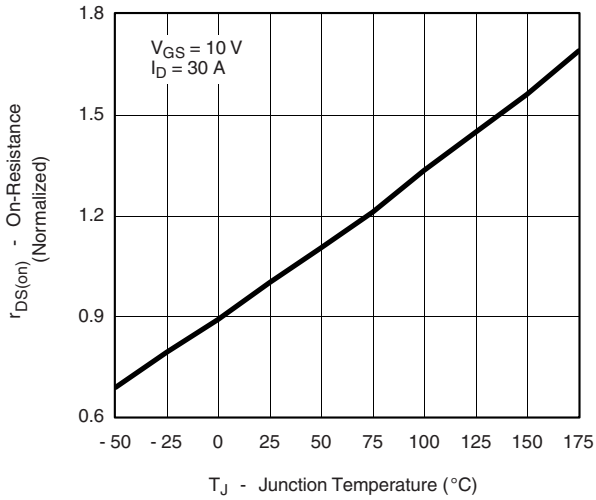
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Independent of operating temperature.
- c. Guaranteed by design, not subject to production testing.

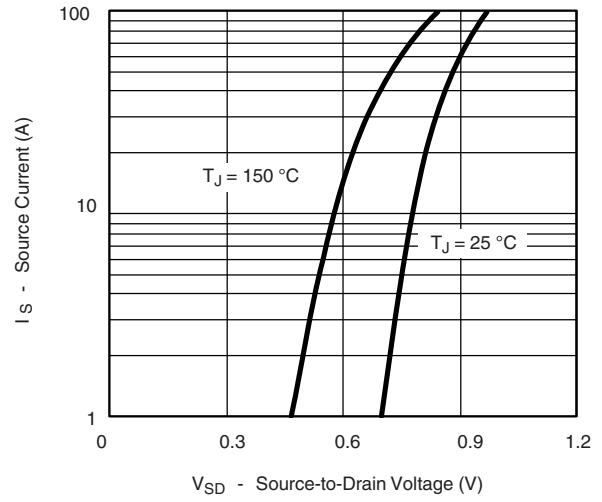
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

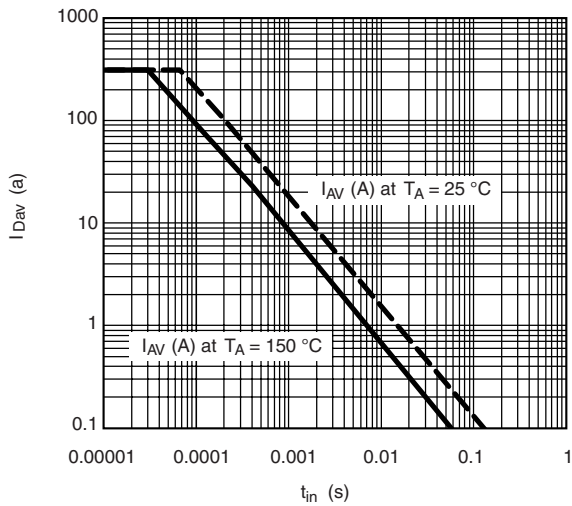
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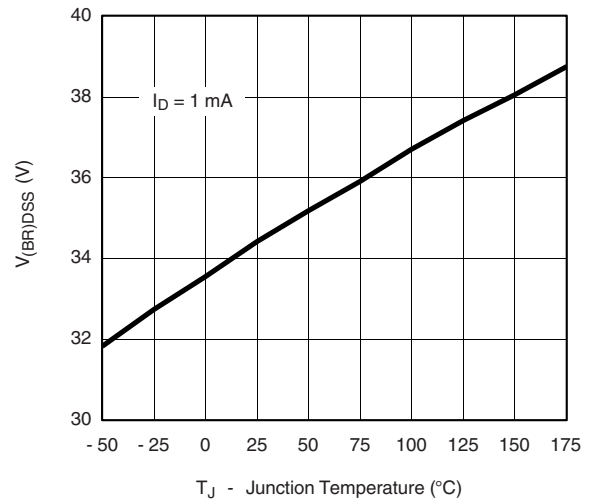
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

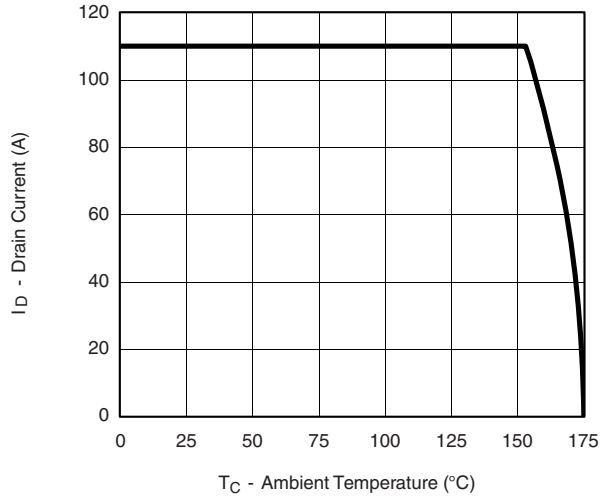


Avalanche Current vs. Time

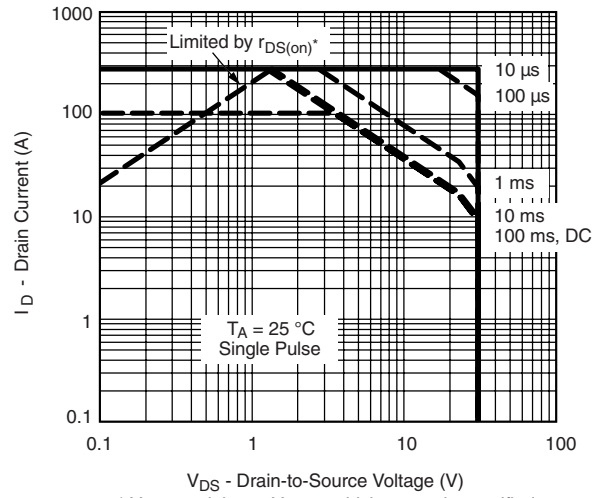


Drain Source Breakdown vs. Junction Temperature

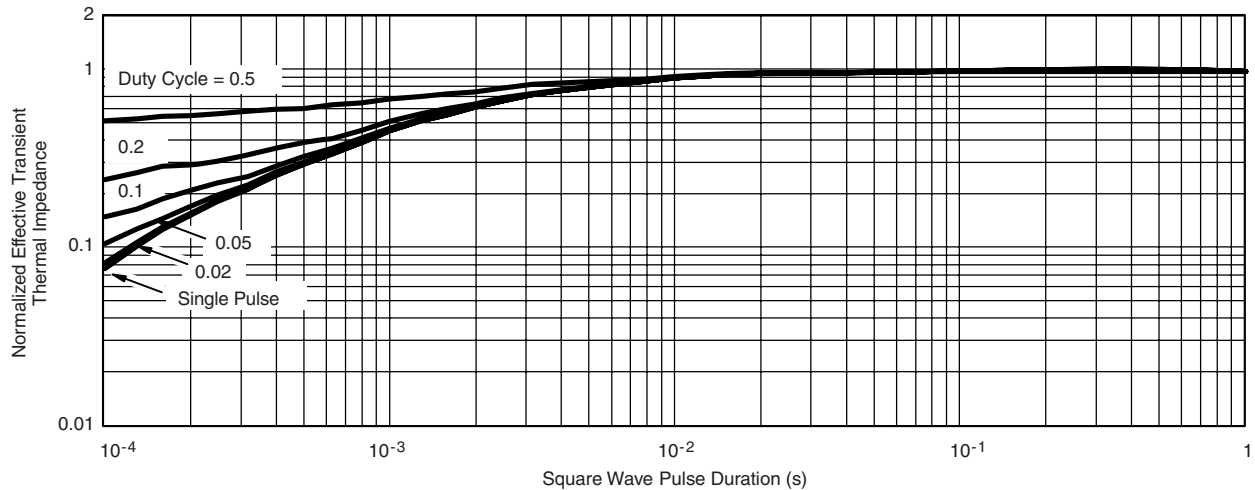
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area
* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case

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